

## N-Channel 100-V (D-S) MOSFET

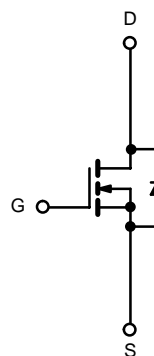
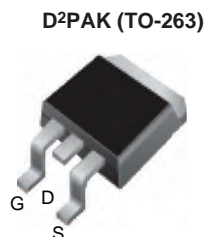
PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
100	0.030 at $V_{GS} = 10$ V	45
	0.035 at $V_{GS} = 4.5$ V	40

### FEATURES

- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- Low Thermal Resistance Package



Available  
**RoHS\***  
COMPLIANT



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	100	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	$T_C = 25$ °C	45	A
		$T_C = 125$ °C	30	
Pulsed Drain Current	$I_{DM}$	135		
Avalanche Current	$I_{AR}$	35		
Repetitive Avalanche Energy <sup>a</sup>	$E_{AR}$	61	mJ	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_C = 25$ °C	127 <sup>b</sup>	W
		$T_A = 25$ °C <sup>c</sup>	3.75	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient	$R_{thJA}$	40	°C/W	(PCB Mount) <sup>c</sup>
Junction-to-Case (Drain)	$R_{thJC}$	1.4		

Notes:

- Duty cycle  $\leq 1$  %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

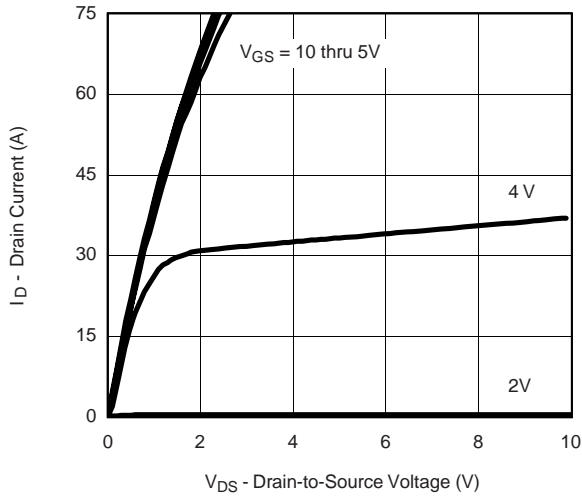
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{SS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	75			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.030		$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 3\text{ A}$		0.035		
		$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.050		
		$V_{GS} = 10\text{ V}, I_D = 3\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.062		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$	10			S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		3100		$\mu\text{F}$
Output Capacitance	$C_{oss}$			410		
Reverse Transfer Capacitance	$C_{rss}$			150		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 40\text{ A}$		35	60	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			11		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			9		
Gate Resistance	$R_G$			1.7		$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 1.25\text{ }\Omega$ $I_D \cong 40\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$		11	20	ns
Rise Time <sup>c</sup>	$t_r$			12	20	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			30	45	
Fall Time <sup>c</sup>	$t_f$			12	20	
<b>Source-Drain Diode Ratings and Characteristics</b> $T_C = 25\text{ }^\circ\text{C}$ <sup>b</sup>						
Continuous Current	$I_S$				40	A
Pulsed Current	$I_{SM}$				120	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 30\text{ A}, V_{GS} = 0\text{ V}$		1.0	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 30\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		60	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			5	8	A
Reverse Recovery Charge	$Q_{rr}$			0.15	0.4	$\mu\text{C}$

Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

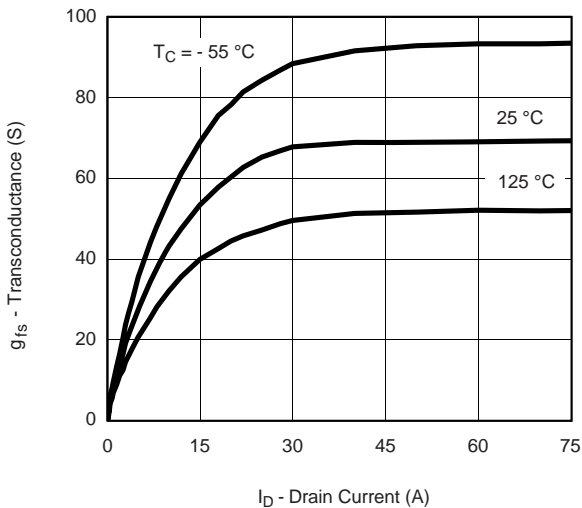
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



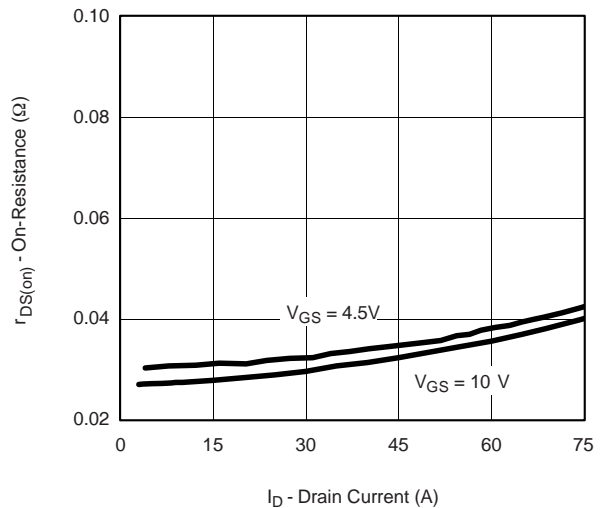
**Output Characteristics**



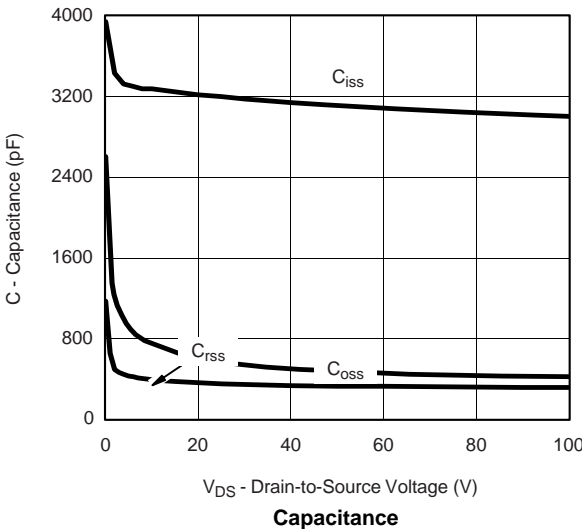
**Transfer Characteristics**



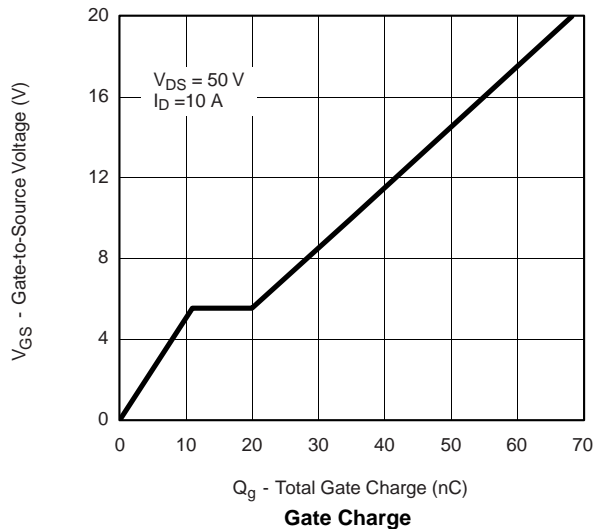
**Transconductance**



**On-Resistance vs. Drain Current**

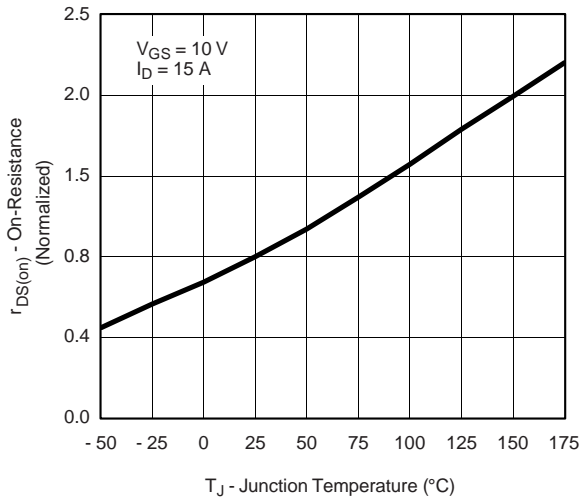


**Capacitance**

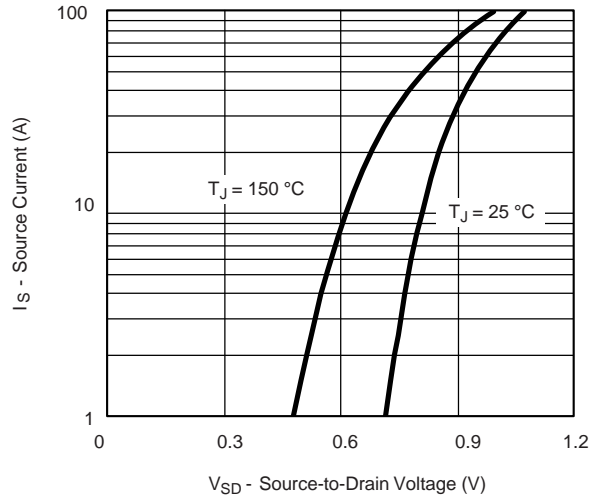


**Gate Charge**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



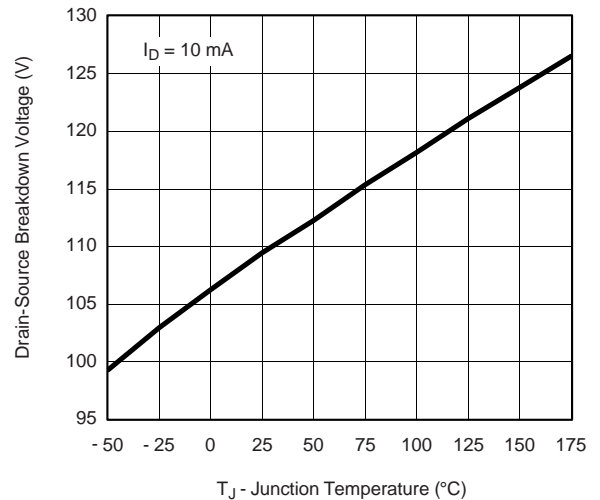
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**Avalanche Current vs. Time**



**Drain-Source Breakdown Voltage vs. Junction Temperature**

**THERMAL RATINGS**



**Maximum Avalanche and Drain Current vs. Case Temperature**



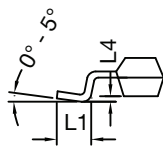
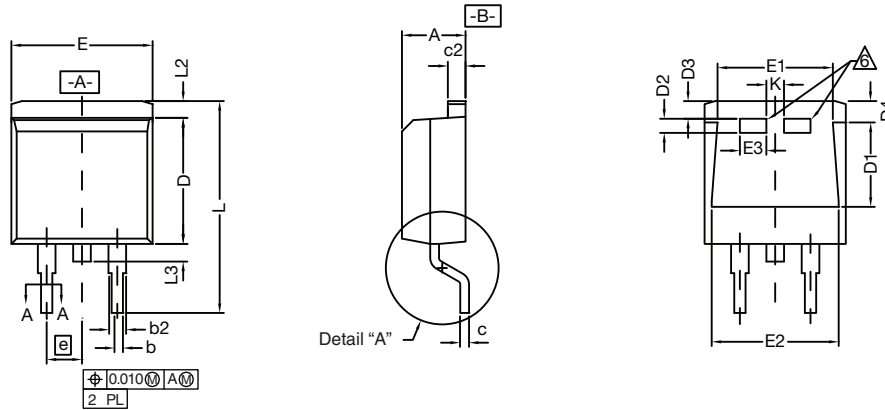
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $r_{DS(on)}$  is specified

**Safe Operating Area**

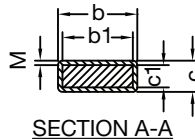


**Normalized Thermal Transient Impedance, Junction-to-Case**

TO-263 (D<sup>2</sup>PAK): 3-LEAD




DETAIL A (ROTATED 90°)



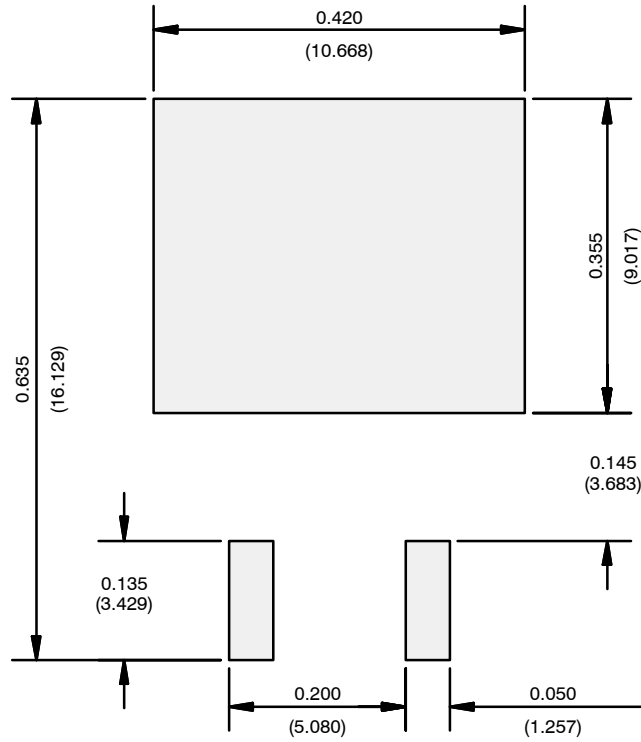
SECTION A-A

DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
-  This feature is for thick lead.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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